16-bit Bus Transceivers with 3-state Outputs

HITACHI

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Description

The HD74ALVCH16245 is designed for asynchronous communication between data buses. The control function implementation minimizes external timing requirements. This device can be used as two 8-bit transceivers or one 16-bit transceiver. It allow data transmission from the A bus to the B bus or from the B bus to the A bus depending upon the logic level at the direction control (DIR) input. The output enable (\overline{OE}) input can be used to disable the device so that the buses are effectively isolated. Active bus hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

Features

- $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$
- Typical V_{OL} ground bounce < 0.8 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.0 V (@ V_{CC} = 3.3 V, T_a = 25°C)
- Bus hold on data inputs eliminates the need for external pullup / pulldown resistors

Function Table

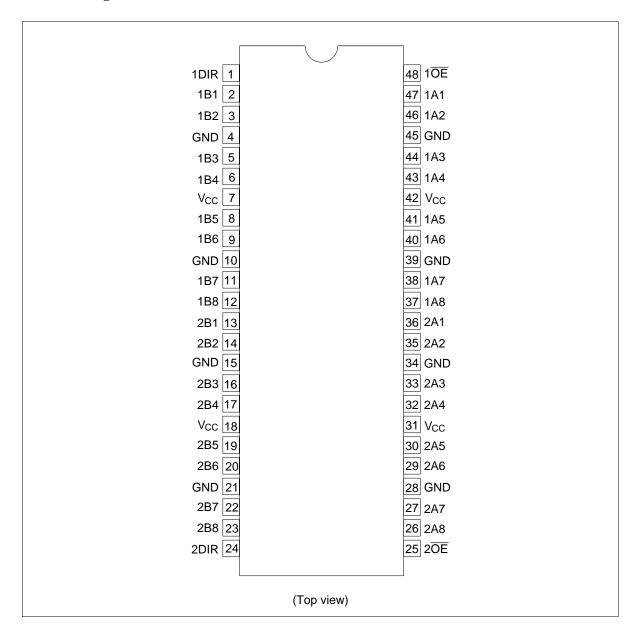
Inputs		Operation
ŌE	DIR	~ 云市坎
L	L	B data to A bus
L	Н	A data to B bus
Н	X	Isolation

H : High level L : Low level

X : Immaterial



Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{cc}	-0.5 to 4.6	V	
Input voltage *1, 2	Vı	-0.5 to 4.6	V	Except I/O ports
		-0.5 to V_{CC} +0.5		I/O ports
Output voltage *1, 2	V _o	-0.5 to V _{cc} +0.5	V	
Input clamp current	I _{IK}	– 50	mA	V ₁ < 0
Output clamp current	I _{ok}	±50	mA	$V_{o} < 0 \text{ or } V_{o} > V_{cc}$
Continuous output current	Io	±50	mA	$V_{o} = 0 \text{ to } V_{cc}$
V _{cc} , GND current / pin	$I_{\rm CC}$ or $I_{\rm GND}$	±100	mA	
Maximum power dissipation at Ta = 55°C (in still air) *3	P _T	0.85	W	TSSOP
Storage temperature	Tstg	-65 to 150	°C	

Notes:

Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating condition" is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

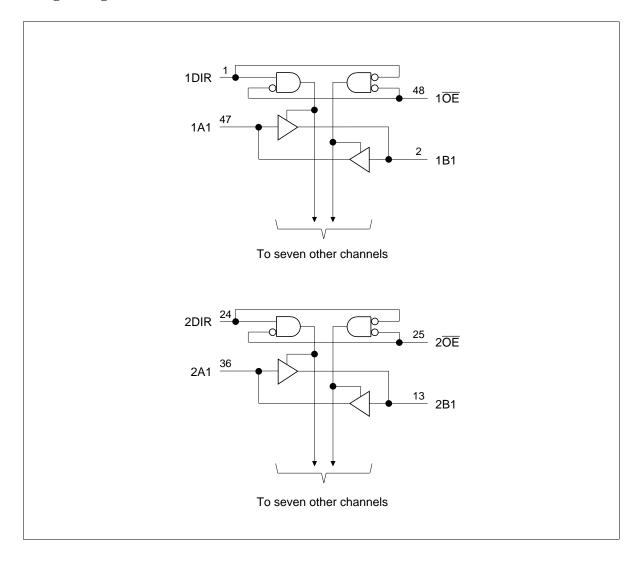
- 1. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.
- 2. This value is limited to 4.6 V maximum.
- 3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage	V _{cc}	2.3	3.6	V	
Input voltage	V _I	0	V _{CC}	V	
Output voltage	Vo	0	V _{CC}	V	
High level output current	I _{OH}	_	-12	mA	V _{CC} = 2.3 V
		_	-12		$V_{CC} = 2.7 \text{ V}$
		_	-24		$V_{CC} = 3.0 \text{ V}$
Low level output current	I _{OL}	_	12	mA	V _{cc} = 2.3 V
		_	12		$V_{CC} = 2.7 \text{ V}$
		_	24		$V_{CC} = 3.0 \text{ V}$
Input transition rise or fall rate	Δt / Δν	0	10	ns / V	
Operating temperature	Та	-40	85	°C	

Note: Unused control inputs must be held high or low to prevent them from floating.

Logic Diagram



Electrical Characteristics ($Ta = -40 \text{ to } 85^{\circ}\text{C}$)

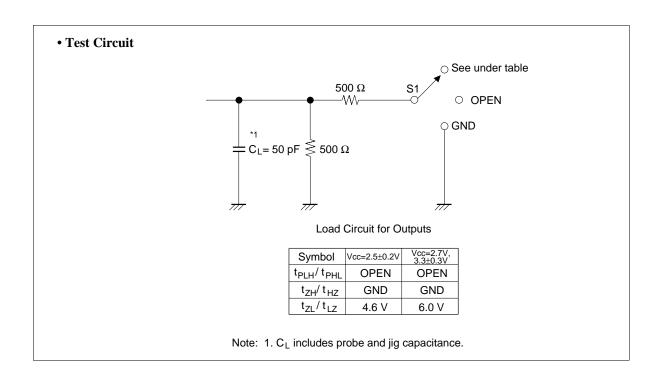
Item	Symbol	$V_{cc}(V)^{*1}$	Min	Max	Unit	Test Conditions
Input voltage	V _{IH}	2.3 to 2.7	1.7	_	V	
		2.7 to 3.6	2.0	_	_	
	V _{IL}	2.3 to 2.7	_	0.7		
		2.7 to 3.6	_	0.8		
Output voltage	V _{OH}	Min to Max	V _{cc} -0.2	_	V	$I_{OH} = -100 \mu A$
		2.3	2.0	_	_	$I_{OH} = -6 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		2.3	1.7	_	_	$I_{OH} = -12 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		2.7	2.2	_	_	$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		3.0	2.4	_	_	$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		3.0	2.0	_	_	$I_{OH} = -24 \text{ mA}, V_{IH} = 2.0 \text{ V}$
	V _{OL}	Min to Max	_	0.2	_	I _{OL} = 100 μA
		2.3	_	0.4		$I_{OL} = 6 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		2.3	_	0.7		$I_{OL} = 12 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		2.7	_	0.4	_	$I_{OL} = 12 \text{ mA}, V_{IL} = 0.8 \text{ V}$
		3.0	_	0.55		$I_{OL} = 24 \text{ mA}, V_{IL} = 0.8 \text{ V}$
Input current	I _{IN}	3.6	_	±5	μΑ	$V_{IN} = V_{CC}$ or GND
	I _{IN (hold)}	2.3	45	_	_	$V_{IN} = 0.7 \text{ V}$
		2.3	-45	_	_	V _{IN} = 1.7 V
		3.0	75	_		V _{IN} = 0.8 V
		3.0	-75	_	_	V _{IN} = 2.0 V
		3.6	_	±500		$V_{IN} = 0 \text{ to } 3.6 \text{ V}$
Off state output current *2 I _{oz}		3.6	_	±10	μΑ	V _{OUT} = V _{CC} or GND
Quiescent supply curre	ent I _{cc}	3.6	_	40	μΑ	$V_{IN} = V_{CC}$ or GND
	ΔI_{cc}	3.0 to 3.6	_	750	μΑ	V_{IN} = one input at (V_{CC} -0.6) V, other inputs at V_{CC} or GND

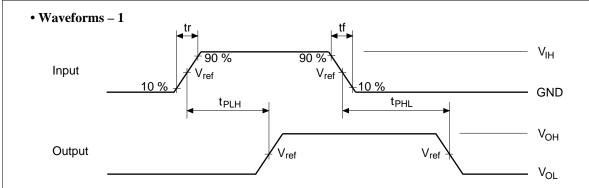
Notes: 1. For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

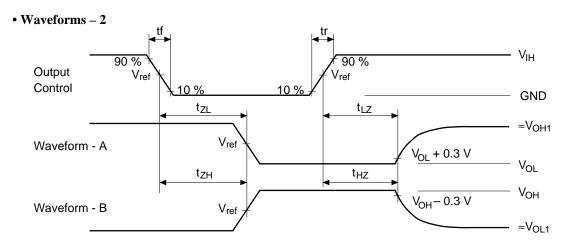
^{2.} For I/O ports, the parameter $\rm I_{\rm oz}$ includes the input leakage current.

Switching Characteristics (Ta = -40 to 85°C)

Item	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH}	2.5±0.2	1.0	_	3.9	ns	A or B	B or A
	$t_{\tiny PHL}$	2.7	_	_	3.6			
		3.3±0.3	1.0	_	3.2			
Output enable time	t _{zH}	2.5±0.2	1.0	_	5.7	ns	ŌĒ	B or A
	t_{zL}	2.7	_	_	5.4			
		3.3±0.3	1.0	_	4.4	_		
Output disable time	t _{HZ}	2.5±0.2	1.0	_	5.2	ns	ŌĒ	B or A
	\mathbf{t}_{LZ}	2.7	_	_	4.6			
		3.3±0.3	1.0	_	4.1			
Input capacitance	C _{IN}	3.3	_	4.0	_	pF	Control inputs	
Output capacitance	C _o	3.3	_	9.0	_	pF	A or B por	rts







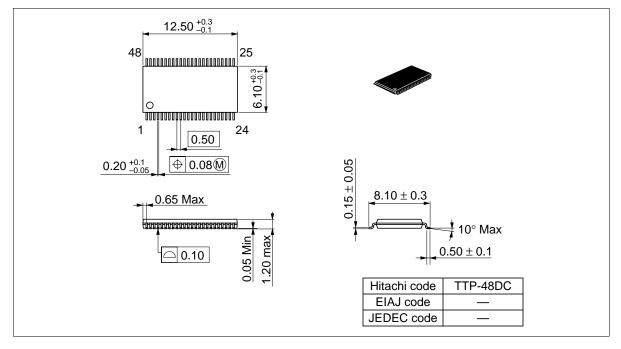
TEST	Vcc=2.5±0.2V	Vcc=2.7V, 3.3±0.3V
V_{IH}	2.3 V	2.7 V
V_{ref}	1.2 V	1.5 V
V _{OH1}	2.3 V	3.0 V
V _{OL1}	GND	GND

Notes: 1. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Zo = 50 Ω , tr \leq 2.5 ns, tf \leq 2.5 ns.

- 2. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 3. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. The output are measured one at a time with one transition per measurement.

Package Dimensions

Unit: mm



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